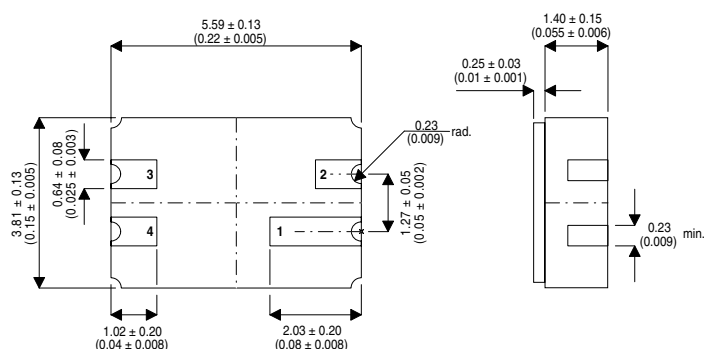


**MECHANICAL DATA**

Dimensions in mm (inches)


**LCC3**

PAD 1 = COLLECTOR    PAD 3 = EMITTER  
 PAD 2 = N/C            PAD 4 = BASE

**SILICON PLANAR NPN HIGH VOLTAGE TRANSISTOR IN A CERAMIC SURFACE MOUNT PACKAGE**
**FEATURES**

- High Voltage
- Ceramic Surface Mount
- Screening Options Available

**ABSOLUTE MAXIMUM RATINGS**

$V_{CBO}$	Collector - Base Voltage ( $I_E = 0$ )	160V
$V_{CEO}$	Collector - Emitter Voltage ( $I_B = 0$ )	160V
$V_{EBO}$	Emitter Base Voltage ( $I_C = 0$ )	5V
$I_C$	Collector Current	100mA
$I_{CM}$	Collector Peak Current	200mA
$P_{tot}$	Total Power Dissipation at $T_{case} \leq 50^\circ C$	5W
$T_{stg}$	Storage Temperature	-55 to $200^\circ C$
$T_j$	Junction Temperature	$200^\circ C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

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## Thermal Data

$R_{th\ j-case}$	Thermal resistance junction - case	max	30°C/W
$R_{th\ j-amb}$	Thermal resistance junction - ambient	max	175°C/W

## Electrical Characteristics

( $T_{amb} = 25^{\circ}C$  Unless otherwise specified)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{(BR)CEO}^*$	Collector–Emitter Breakdown Voltage	$I_C = 10mA$	$I_B = 0$	160	V	
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	$I_C = 100\mu A$	$I_E = 0$	160		
$V_{(BR)EBO}$	Emitter - Base Breakdown Voltage	$I_C = 0$	$I_E = 100\mu A$	5		
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 100V$	$I_E = 0$		50	nA
$V_{CE(sat)}^*$	Collector – Emitter Saturation Voltage	$I_C = 30mA$	$I_B = 6mA$		1	V
$h_{FE}^*$	DC Current Gain	$I_C = 30mA$	$I_B = 10V$	25		—
$f_t$	Transition Frequency	$I_C = 15mA$	$V_{CE} = 10V$		90	MHz
$C_{re}$	Reverse Capacitance	$I_C = 0$ $f = 1MHz$	$V_{CE} = 30V$		3	pF

\* Pulsed test  $t_p = 300\mu s$  ,  $\delta = 1\%$